

General Description

The MAX7033 fully integrated low-power CMOS superheterodyne receiver is ideal for receiving amplitudeshift-keyed (ASK) data in the 300MHz to 450MHz frequency range. The receiver has an RF input signal range of -114dBm to 0dBm. With few external components and a low-current power-down mode, it is ideal for cost-sensitive and power-sensitive applications typical in the automotive and consumer markets. The MAX7033 consists of a low-noise amplifier (LNA), a fully differential image-rejection mixer, an on-chip phaselocked loop (PLL) with integrated voltage-controlled oscillator (VCO), a 10.7MHz IF limiting amplifier stage with received-signal-strength indicator (RSSI), and analog baseband data-recovery circuitry. The MAX7033 also has a discrete one-step automatic gain control (AGC) that reduces the LNA gain by 35dB when the RF input signal exceeds -62dBm. The AGC circuitry offers an externally controlled hold feature.

The MAX7033 is available in a 28-pin TSSOP package and is specified over the extended (-40°C to +105°C) temperature range.

Applications

Automotive Remote Keyless Entry Security Systems Garage Door Openers Home Automation Remote Controls Local Telemetry Wireless Sensors

Typical Application Circuit appears at end of data sheet.

Features

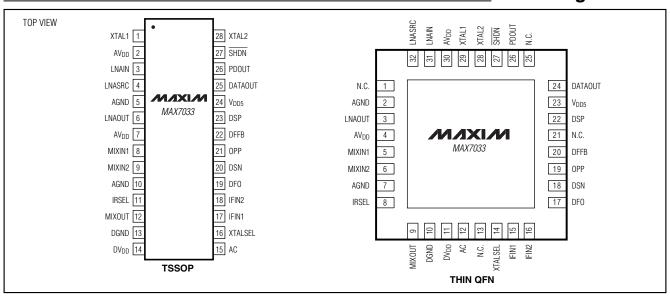
- ♦ Optimized for 315MHz or 433MHz Band
- ♦ Operates from Single +3.3V or +5.0V Supplies
- ♦ High Dynamic Range with On-Chip AGC
- **♦ AGC Hold Circuit**
- ♦ 1ms AGC Release Time
- **♦** Selectable Image-Rejection Center Frequency
- ♦ Selectable x64 or x32 f_{LO}/f_{XTAL} Ratio
- **♦ Low 5.2mA Operating Supply Current**
- ♦ <3.5µA Low-Current Power-Down Mode for **Efficient Power Cycling**
- ♦ 250µs Startup Time
- ♦ Built-In 44dB RF Image Rejection
- ♦ Better than -114dBm Receive Sensitivity
- ◆ -40°C to +105°C Operation

Ordering Information

PART	TEMP RANGE	PIN-PACKAGE
MAX7033EUI	-40°C to +105°C	28 TSSOP
MAX7033ETJ*	-40°C to +105°C	32 Thin QFN-EP**

^{*}Future product—contact factory for availability.

Pin Configurations



MIXIM

Maxim Integrated Products 1

^{**}EP = Exposed paddle.

ABSOLUTE MAXIMUM RATINGS

VDD5 to AGND -0.3V to +6.0V AVDD to AGND -0.3V to +4.0V DVDD to DGND -0.3V to +4.0V AGND to DGND -0.1V to +0.1V IRSEL, DATAOUT, XTALSEL, -0.3V to (VDD5 + 0.3V) All Other Pins to AGND -0.3V to (DVDD + 0.3V)	Continuous Power Dissipation (T _A = +70°C) 28-Pin TSSOP (derate 12.8mW/°C above +70°C)1025.6mW 32-Thin QFN (derate 21.3mW/°C above +70°C)1702.1mW Operating Temperature Range40°C to +105°C Junction Temperature+150°C Storage Temperature Range60°C to +150°C Lead Temperature (soldering 10s)+300°C
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Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

DC ELECTRICAL CHARACTERISTICS (+3.3V OPERATION)

(*Typical Application Circuit*, $AV_{DD} = DV_{DD} = V_{DD5} = +3.0V$ to +3.6V, no RF signal applied, $T_A = -40^{\circ}C$ to $+105^{\circ}C$, unless otherwise noted. Typical values are at $AV_{DD} = DV_{DD} = V_{DD5} = +3.3V$ and $T_A = +25^{\circ}C$.) (Note 1)

PARAMETER	SYMBOL	CC	ONDITIONS	MIN	TYP	MAX	UNITS
Supply Voltage	AV _{DD} , DV _{DD}	+3.3V nominal su	oply voltage	3.0	3.3	3.6	V
Supply Current	I _{DD}	VSHDN = DVDD	f _{RF} = 315MHz		5.2	6.23	mA
Supply Current	טטי	V SHDN - DVDD	$f_{RF} = 433MHz$		5.7	6.88	IIIA
Shutdown Supply Current	louin	$V\overline{SHDN} = 0V,$	f _{RF} = 315MHz		2.6		
Shutdown Supply Current	ISHDN	VXTALSEL = 0V	$f_{RF} = 433MHz$		3.5	8.0	μΑ
Input-Voltage Low	V _{IL}					0.4	V
Input-Voltage High	V _{IH}			DV _{DD} - 0.4			V
Input Logic Current High	IIH				10		μΑ
		f _{RF} = 433MHz, V _{II}	$f_{RF} = 433 MHz$, $V_{IRSEL} = V_{DD5}$ $f_{RF} = 375 MHz$, $V_{IRSEL} = V_{DD5} / 2$				
Image-Reject Select Voltage (Note 2)		f _{RF} = 375MHz, V _{II}				V _{DD5} - 1.0	V
		f _{RF} = 315MHz, V _{II}	RSEL = 0V			0.4	
DATAOUT Output-Voltage Low	V _{OL}	I _{SINK} = 10µA			0.125		V
DATAOUT Output-Voltage High	V _{OH}	ISOURCE = 10µA			DV _{DD} - 0.125		V

DC ELECTRICAL CHARACTERISTICS (+5.0V OPERATION)

(*Typical Application Circuit*, V_{DD5} = +4.5V to +5.5V, no RF signal applied, T_A = -40°C to +105°C, unless otherwise noted. Typical values are at V_{DD5} = +5.0V and T_A = +25°C.) (Note 1)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	МАХ	UNITS
Supply Voltage	V _{DD5}	+5.0V nominal su	+5.0V nominal supply voltage		5.0	5.5	V
Supply Current	lee	V SHDN = V _{DD5}	f _{RF} = 315MHz		5.2	6.4	mA
	IDD		$f_{RF} = 433MHz$		5.7	6.76	
Clausted annua Consent of Consent	l=v=v=	$V\overline{SHDN} = 0V$,	$f_{RF} = 315MHz$		3.7		
Shutdown Supply Current	ISHDN	VXTALSEL = 0V	$f_{RF} = 433MHz$		4.2	9.0	μA
Input-Voltage Low	V _{IL}					0.4	V

DC ELECTRICAL CHARACTERISTICS (+5.0V OPERATION) (continued)

(*Typical Application Circuit*, $V_{DD5} = +4.5V$ to +5.5V, no RF signal applied, $T_A = -40^{\circ}C$ to $+105^{\circ}C$, unless otherwise noted. Typical values are at $V_{DD5} = +5.0V$ and $T_A = +25^{\circ}C$.) (Note 1)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Input-Voltage High	VIH		V _{DD5} - 0.4			V
Input Logic Current High	lін			15		μΑ
		f _{RF} = 433MHz, V _{IRSEL} = V _{DD5}	V _{DD5} - 0.4			
Image-Reject Select Voltage (Note 2)		f _{RF} = 375MHz, V _{IRSEL} = V _{DD5} / 2	1.1		V _{DD5} - 1.5	V
		f _{RF} = 315MHz, V _{IRSEL} = 0V			0.4	
DATAOUT Output-Voltage Low	V _{OL}	I _{SINK} = 10µA		0.125		V
DATAOUT Output-Voltage High	V _{OH}	I _{SOURCE} = 10μA		V _{DD5} - 0.125		V

AC ELECTRICAL CHARACTERISTICS

(Typical Application Circuit, $AV_{DD} = DV_{DD5} = +3.0V$ to +3.6V, all RF inputs are referenced to 50Ω , $f_{RF} = 315MHz$, $T_A = -40^{\circ}C$ to $+105^{\circ}C$, unless otherwise noted. Typical values are at $AV_{DD} = DV_{DD5} = +3.3V$ and $T_A = +25^{\circ}C$.) (Note 1)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
GENERAL CHARACTERISTICS							
Startup Time	ton	Time for valid signa = DV _{DD}	I detection after VSHDN		250		μs
Receiver Input Frequency	f _{RF}			300		450	MHz
Maximum Receiver Input Level		Modulation depth >	18dB		0		dBm
Sensitivity (Note 3)		Average carrier pov	ver level		-120		dBm
Sensitivity (Note 3)		Peak power level			-114		UDIII
AGC Hysteresis		LNA gain from low t	o high		8		dB
Add Hysteresis		Switching time from	low to high gain		1		ms
Maximum Data Rate		Manchester coded		33		kbps	
Maximum Data Hate		NRZ coded		66		Nopo	
LNA IN HIGH-GAIN MODE				_			
			f _{RF} = 433MHz		1 - j3.4		
Input Impedance	Z _{IN_LNA}	Normalized to 50Ω	f _{RF} = 375MHz		1 - j3.9		
			$f_{RF} = 315MHz$		1 - j4.7		
1dB Compression Point	P1dB _{LNA}				-22		dBm
Input-Referred 3rd-Order Intercept	IIP3 _{LNA}				-12		dBm
LO Signal Feedthrough to Antenna					-80		dBm
Output Impedance	Z _{OUT_LNA}	Normalized to 50Ω			0.12 - j4.4		
Noise Figure	NF _{LNA}				3		dB



AC ELECTRICAL CHARACTERISTICS (continued)

(Typical Application Circuit, AV_{DD} = DV_{DD} = V_{DD5} = +3.0V to +3.6V, all RF inputs are referenced to 50Ω , f_{RF} = 315MHz, T_A = -40°C to +105°C, unless otherwise noted. Typical values are at AV_{DD} = DV_{DD} = V_{DD5} = +3.3V and T_A = +25°C.) (Note 1)

PARAMETER	SYMBOL	CON	DITIONS	MIN TYP I	MAX UNIT
LNA IN LOW-GAIN MODE	.			·	
			f _{RF} = 433MHz	1 - j3.4	
Input Impedance	Z _{IN_LNA}	Normalized to 50Ω (Note 4)	f _{RF} = 375MHz	1 - j3.9	
		(11016-4)	f _{RF} = 315MHz	1 - j4.7	
1dB Compression Point	P1dB _{LNA}			-10	dBn
Input-Referred 3rd-Order Intercept	IIP3 _{LNA}			-7	dBn
LO Signal Feedthrough to Antenna				-80	dBn
Output Impedance	Z _{OUT_LNA}	Normalized to 50Ω		0.4	
Noise Figure	NFLNA			3	dB
Voltage-Gain Reduction		AGC enabled (depe	ends on tank Q)	35	dB
MIXER	•	•	*	1	<u> </u>
Input Impedance	Z _{IN_MIX}	Normalized to 50Ω		0.25 - j2.4	
Input-Referred 3rd-Order Intercept	IIP3 _{MIX}			-18	dBn
Output Impedance	Z _{OUT_MIX}			330	Ω
Noise Figure	NF _{MIX}			16	dB
		f _{RF} = 433MHz, V _{IRSEL} = DV _{DD} f _{RF} = 375MHz, V _{IRSEL} = DV _{DD} / 2		42	
Image Rejection				44	dB
(Not Including LNA Tank)		f _{RF} = 315MHz, V _{IRSI}	EL = 0V	44	
			LNA in high-gain mode	48	
LNA/Mixer Voltage Gain		330Ω IF filter load	LNA in low-gain mode	13	dB
INTERMEDIATE FREQUENCY	/ (IF)	1	-	-	<u>'</u>
Input Impedance	Z _{IN_IF}			330	Ω
Operating Frequency	fıF	Bandpass response		10.7	MH
3dB Bandwidth				10	MH
RSSI Linearity				±0.5	dB
RSSI Dynamic Range				80	dB
DCCLLovel		P _{RFIN} < -120dBm		1.15	1/
RSSI Level		P _{RFIN} > 0dBm, AGC	enabled	2.2	V
ACC Throshold		LNA gain from low to	o high	1.39	V
AGC Threshold		LNA gain from high to low		1.98	V
DATA FILTER					
Maximum Bandwidth				50	kHz
DATA SLICER					
Comparator Bandwidth				100	kHz

AC ELECTRICAL CHARACTERISTICS (continued)

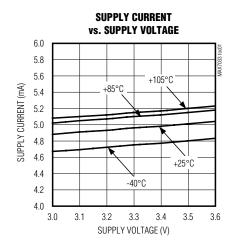
(Typical Application Circuit, $AV_{DD} = DV_{DD} = V_{DD5} = +3.0V$ to +3.6V, all RF inputs are referenced to 50Ω , $f_{RF} = 315MHz$, $T_A = -40^{\circ}C$ to $+105^{\circ}C$, unless otherwise noted. Typical values are at $AV_{DD} = DV_{DD5} = +3.3V$ and $T_A = +25^{\circ}C$.) (Note 1)

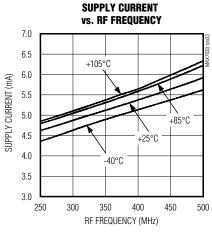
PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS	
Maximum Load Capacitance	CLOAD				10		рF	
Output High Voltage					V_{DD5}		V	
Output Low Voltage					0		V	
CRYSTAL OSCILLATOR	CRYSTAL OSCILLATOR							
		f _{RF} = 433MHz	VXTALSEL = 0V		6.6128		- MHz	
Crystal Fraguescy (Note F)	6		VXTALSEL = VDD5		13.2256			
Crystal Frequency (Note 5)	fxtal	f _{RF} = 315MHz	VXTALSEL = 0V		4.7547			
			VXTALSEL = VDD5		9.5094			
Crystal Tolerance					50		ppm	
Input Capacitance		From each pin to ground			6.2		рF	

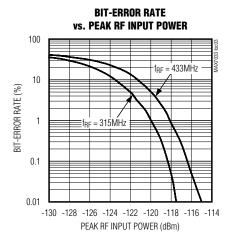
- Note 1: 100% tested at T_A = +25°C. Guaranteed by design and characterization over temperature.
- **Note 2:** IRSEL is internally set to 375MHz IR mode. It can be left open when the 375MHz image-rejection setting is desired. Bypass to AGND with a 1nF capacitor in a noisy environment.
- Note 3: BER = 2 x 10-3, Manchester encoded, data rate = 4kbps, IF bandwidth = 280kHz.
- **Note 4:** Input impedance is measured at the LNAIN pin. Note that the impedance includes the 15nH inductive degeneration connected from the LNA source to ground. The equivalent input circuit is 50Ω in series with 2.2pF.
- Note 5: Crystal oscillator frequency for other RF carrier frequency within the 300MHz to 450MHz range is (f_{RF} 10.7MHz) / 64 for XTALSEL = 0V, and (f_{RF} 10.7MHz) / 32 for XTALSEL = V_{DD5}.

Typical Operating Characteristics

(Typical Application Circuit, AVDD = DVDD = VDD5 = +3.3V, fRF = 315MHz, TA = +25°C, unless otherwise noted.)

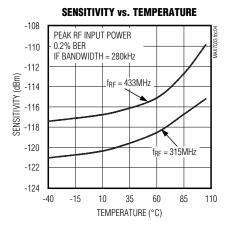


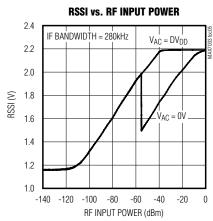


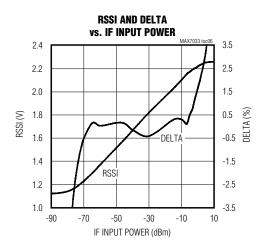


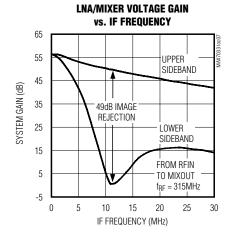
Typical Operating Characteristics (continued)

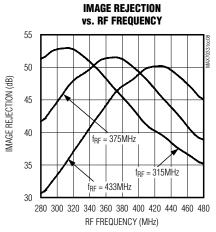
(Typical Application Circuit, $AV_{DD} = DV_{DD} = V_{DD5} = +3.3V$, $f_{RF} = 315MHz$, $T_A = +25^{\circ}C$, unless otherwise noted.)

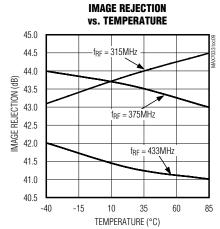






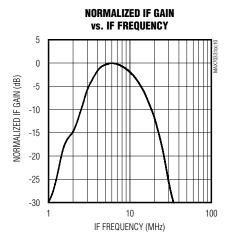


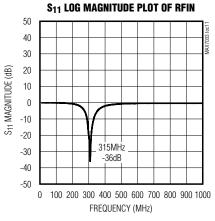


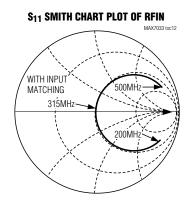


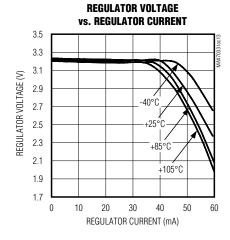
Typical Operating Characteristics (continued)

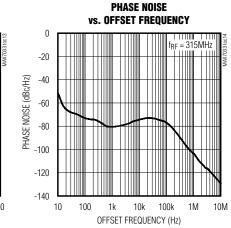
(Typical Application Circuit, $AV_{DD} = DV_{DD} = V_{DD5} = +3.3V$, $f_{RF} = 315MHz$, $T_A = +25^{\circ}C$, unless otherwise noted.)

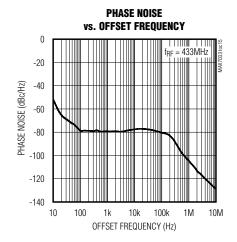












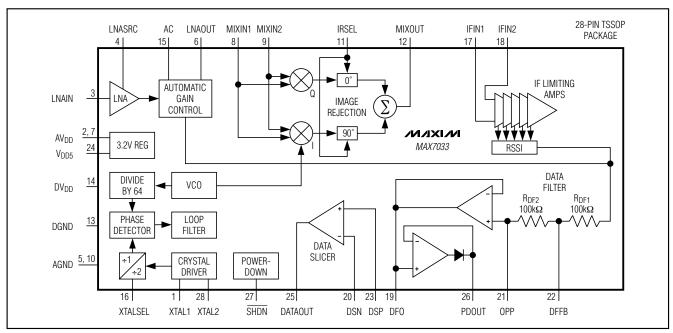
Pin Description

Р	PIN		
TSSOP	THIN QFN	NAME	FUNCTION
1	29	XTAL1	Crystal Input 1 (See the <i>Phase-Locked Loop</i> section)
2, 7	4, 30	AV _{DD}	Positive Analog Supply Voltage. For +5V operation, AV _{DD} is connected to an on-chip +3.2V low-dropout regulator. Both AV _{DD} pins must be externally connected to each other. Bypass each pin to AGND with a 0.01µF capacitor as close to the pin as possible (see the <i>Typical Application Circuit</i>).
3	31	LNAIN	Low-Noise Amplifier Input (See the Low-Noise Amplifier section)
4	32	LNASRC	Low-Noise Amplifier Source for External Inductive Degeneration. Connect inductor to ground to set the LNA input impedance (see the <i>Low-Noise Amplifier</i> section).
5, 10	2, 7	AGND	Analog Ground
6	3	LNAOUT	Low-Noise Amplifier Output. Connect to mixer input through an LC tank filter (see the Low-Noise Amplifier section).
8	5	MIXIN1	1st Differential Mixer Input. Connect to LC tank filter from LNAOUT.
9	6	MIXIN2	2nd Differential Mixer Input. Connect through a 100pF capacitor to AVDD side of the LC tank.
11	8	IRSEL	Image-Rejection Select. Set V _{IRSEL} = 0V to center image rejection at 315MHz. Leave IRSEL unconnected to center image rejection at 375MHz. Set V _{IRSEL} = V _{DD5} to center image rejection at 433MHz.
12	9	MIXOUT	330Ω Mixer Output. Connect to the input of the 10.7MHz bandpass filter.
13	10	DGND	Digital Ground
14	11	DV _{DD}	Positive Digital Supply Voltage. Connect to AV_{DD} . Bypass to DGND with a $0.01\mu F$ capacitor as close to the pin as possible.
15	12	AC	Automatic Gain Control. See Figure 1. Internally pulled down to AGND with a $100 k\Omega$ resistor.
16	14	XTALSEL	Crystal Divider Ratio Select. Drive XTALSEL low to select divider ratio of 64, or drive XTALSEL high to select divider ratio of 32.
17	15	IFIN1	1st Differential Intermediate-Frequency Limiter Amplifier Input. Bypass to AGND with a 1500pF capacitor as close to the pin as possible.
18	16	IFIN2	2nd Differential Intermediate-Frequency Limiter Amplifier Input. Connect to the output of a 10.7MHz bandpass filter.
19	17	DFO	Data Filter Output
20	18	DSN	Negative Data Slicer Input
21	19	OPP	Noninverting Op-Amp Input for the Sallen-Key Data Filter
22	20	DFFB	Data-Filter Feedback Node. Input for the feedback of the Sallen-Key data filter.
23	22	DSP	Positive Data Slicer Input
24	23	$V_{\rm DD5}$	+5V Supply Voltage. For +5V operation, V_{DD5} is the input to an on-chip voltage regulator whose +3.2V output drives AV_{DD} .
25	24	DATAOUT	Digital Baseband Data Output
26	26	PDOUT	Peak-Detector Output

Pin Description (continued)

Р	PIN NAME		FUNCTION
TSSOP	THIN QFN	INAIVIE	FUNCTION
27	27	SHDN	Power-Down Select Input. Drive high to power up the IC. Internally pulled down to AGND with a $100 k\Omega$ resistor.
28	28	XTAL2	Crystal Input 2. Can also be driven with an external reference oscillator. (See the <i>Crystal Oscillator</i> section.)
_	1, 13, 21, 25	N.C	No Connection

Functional Diagram



Detailed Description

The MAX7033 CMOS superheterodyne receiver and a few external components provide the complete receive chain from the antenna to the digital output data. Depending on signal power and component selection, data rates as high as 33kbps Manchester (66kbps NRZ) can be achieved.

The MAX7033 is designed to receive binary ASK data modulated in the 300MHz to 450MHz frequency range. ASK modulation uses a difference in amplitude of the carrier to represent logic 0 and logic 1 data.

Voltage Regulator

For operation with a single +3.0V to +3.6V supply voltage, connect AVDD, DVDD, and VDD5 to the supply voltage.

For operation with a single +4.5V to +5.5V supply voltage, connect VDD5 to the supply voltage. An on-chip voltage regulator drives one of the AVDD pins to approximately +3.2V. For proper operation, DVDD and both AVDD pins must be connected together. Bypass DVDD and both AVDD pins to AGND with 0.01 μ Capacitors placed as close to the pins as possible.

Low-Noise Amplifier

The LNA is an nMOS cascode amplifier with off-chip inductive degeneration, with a 3.0dB noise figure and an IIP3 of -12dBm. The gain and noise figures are dependent on both the antenna matching network at the LNA input and the LC tank network between the LNA output and the mixer inputs.

The off-chip inductive degeneration is achieved by connecting an inductor from LNASRC to AGND. This inductor sets the real part of the input impedance at LNAIN, allowing for a more flexible input impedance match, such as a typical PC board trace antenna. A nominal value for this inductor with a 50Ω input impedance is 15nH, but is affected by PC board trace.

The LC tank filter connected to LNAOUT comprises L3 and C2 (see the *Typical Application Circuit*). Select L3 and C2 to resonate at the desired RF input frequency. The resonant frequency is given by:

$$f_{RF} = \frac{1}{2\pi\sqrt{L_{TOTAL} \times C_{TOTAL}}}$$

where:

LTOTAL = L3 + LPARASITICS.

CTOTAL = C2 + CPARASITICS.

LPARASITICS and CPARASITICS include inductance and capacitance of the PC board traces, package pins, mixer input impedance, LNA output impedance, etc. These parasitics at high frequencies cannot be ignored, and can have a dramatic effect on the tank filter center frequency. Lab experimentation should be done to optimize the center frequency of the tank.

Automatic Gain Control

When the AC pin is low, the automatic gain-control (AGC) circuit monitors the RSSI output. As the RSSI output reaches 1.98V, which corresponds to RF input level of -62dBm, the AGC switches on the LNA gain

reduction resistor. The resistor reduces the LNA gain by 35dB, thereby reducing the RSSI output by about 500mV. The LNA resumes high-gain mode when the RSSI level drops back below 1.39V (approximately -70dBm at RF input) for 1ms. The AGC has a hysteresis of 8dB. With the AGC function, the MAX7033 can reliably produce an ASK output for RF input levels up to 0dBm with modulation depth of 18dB.

When the AC pin is high and SHDN goes high, the AGC circuit is disabled and the LNA is always in highgain mode. The AGC function can be resumed by bringing the AC pin low when SHDN is high.

The MAX7033 features an AGC lock function that is asserted when the level at the AC pin transitions from low to high while \$\overline{SHDN}\$ is high. Locking the AGC locks the LNA in the current gain state. As shown in Figure 1, the AGC lock function can be enabled or disabled as long as the \$\overline{SHDN}\$ pin is high. Changing the state of AC when \$\overline{SHDN}\$ is low has no effect.

Mixer

A unique feature of the MAX7033 is the integrated image rejection of the mixer. This device eliminates the need for a costly front-end SAW filter for most applications. Advantages of not using a SAW filter are increased sensitivity, simplified antenna matching, less board space, and lower cost.

The mixer cell is a pair of double balanced mixers that perform an IQ downconversion of the RF input to the 10.7MHz IF from a low-side injected LO (i.e., $f_{LO} = f_{RF} - f_{IF}$). The image-rejection circuit then combines these signals to achieve 44dB of image rejection. Low-side

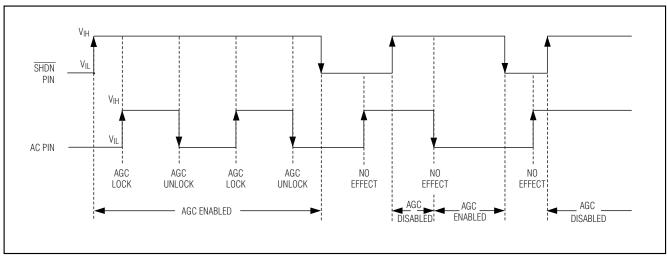


Figure 1. AGC Lock Activation Cycles

injection is required due to the on-chip image-rejection architecture. The IF output is driven by a source follower biased to create a driving-point impedance of 330Ω ; this provides a good match to the off-chip 330Ω ceramic IF filter.

The IRSEL pin is a logic input that selects one of the three possible image-rejection frequencies. When $V_{IRSEL} = 0V$, the image rejection is tuned to 315MHz. $V_{IRSEL} = V_{DD5}$ / 2 tunes the image rejection to 375MHz, and $V_{IRSEL} = V_{DD5}$ tunes the image rejection to 433MHz. The IRSEL pin is internally set to V_{DD5} / 2 (image rejection at 375MHz) when it is left unconnected, thereby eliminating the need for an external V_{DD5} / 2 voltage.

Phase-Locked Loop

The PLL block contains a phase detector, charge pump, integrated loop filter, VCO, asynchronous 64x clock divider, and crystal oscillator driver. Besides the crystal, this PLL does not require any external components. The VCO generates a low-side LO. The relationship between the RF, IF, and reference frequencies is given by:

$$f_{REF} = \frac{f_{RF} - f_{IF}}{32 \times M}$$

where:

M = 1 (VXTALSEL = VDD5) or 2 (VXTALSEL = 0V)

To allow the smallest possible IF bandwidth (for best sensitivity), minimize the tolerance of the reference crystal.

Intermediate Frequency and RSSI

The IF section presents a differential 330Ω load to provide matching for the off-chip ceramic filter. The six internal AC-coupled limiting amplifiers produce an overall gain of approximately 65dB, with a bandpass-filter-type response centered near the 10.7MHz IF frequency with a 3dB bandwidth of approximately 10MHz. The RSSI circuit demodulates the IF by producing a DC output proportional to the log of the IF signal level, with a slope of approximately 14.2mV/dB (see the *Typical Operating Characteristics*).

_Applications Information

Crystal Oscillator

The crystal oscillator in the MAX7033 is designed to present a capacitance of approximately 3pF between the XTAL1 and XTAL2. If a crystal designed to oscillate with a different load capacitance is used, the crystal is pulled away from its stated operating frequency, introducing an error in the reference frequency. Crystals

Table 1. Component Values for Typical Application Circuit

COMPONENT	VALUE FOR f _{RF} = 433MHz	VALUE FOR f _{RF} = 315MHz	DESCRIPTION
L1	56nH	120nH	TOKO LL1608-FH
L2	15nH	15nH	Murata LQP11A
L3	15nH	27nH	Murata LQP11A
C1	100pF	100pF	5%
C2	2pF	4pF	± 0.1pF
C3	100pF	100pF	5%
C4	100pF	100pF	5%
C5	1500pF	1500pF	10%
C6	220pF	220pF	5%
C7	470pF	470pF	5%
C8	0.47µF	0.47µF	20%
C9	220pF	220pF	10%
C10	0.01µF	0.01µF	20%
C11	0.01µF	0.01µF	20%
C12	15pF	15pF	Depends on XTAL
C13	15pF	15pF	Depends on XTAL
R1	5.1kΩ	5.1kΩ	5%
X1	6.5984MHz	4.7547MHz	_
X2	10.7MHz ceramic filter	10.7MHz ceramic filter	Murata SFECV10.7 series

designed to operate with higher differential load capacitance always pull the reference frequency higher. For example, a 4.7547MHz crystal designed to operate with a 10pF load capacitance oscillates at 4.7563MHz with the MAX7033, causing the receiver to be tuned to 315.1MHz rather than 315.0MHz, an error of about 100kHz, or 320ppm.

In actuality, the oscillator pulls every crystal. The crystal's natural frequency is really below its specified frequency, but when loaded with the specified load capacitance, the crystal is pulled and oscillates at its specified frequency. This pulling is already accounted for in the specification of the load capacitance. Additional pulling can be calculated if the electrical parameters of the crystal are known. The frequency pulling is given by:

$$f_P = \frac{C_M}{2} \left(\frac{1}{C_{CASE} + C_{LOAD}} - \frac{1}{C_{CASE} + C_{SPEC}} \right) \times 10^6$$

where:

fp is the amount the crystal frequency pulled in ppm.

C_M is the motional capacitance of the crystal.

CCASE is the case capacitance.

CSPEC is the specified load capacitance.

CLOAD is the actual load capacitance.

When the crystal is loaded as specified, i.e., $C_{LOAD} = C_{SPEC}$, the frequency pulling equals zero.

It is possible to use an external reference oscillator in place of a crystal to drive the VCO. AC-couple the external oscillator to XTAL2 with a 1000pF capacitor. Drive XTAL2 with a signal level of approximately -10dBm. AC-couple XTAL1 to ground with a 1000pF capacitor.

Data Filter

The data filter is implemented as a 2nd-order lowpass Sallen-Key filter. The pole locations are set by the combination of two on-chip resistors and two external capacitors. Adjusting the value of the external capacitors changes the corner frequency to optimize for different data rates. The corner frequency should be set to approximately 1.5 times the fastest expected data rate from the transmitter. Keeping the corner frequency near the data rate rejects any noise at higher frequencies, resulting in an increase in receiver sensitivity.

The configuration shown in Figure 2 can create a Butterworth or Bessel response. The Butterworth filter offers a very flat amplitude response in the passband and a rolloff rate of 40dB/decade for the two-pole filter.

The Bessel filter has a linear phase response, which works well for filtering digital data. To calculate the value of C5 and C6, use the following equations, along with the coefficients in Table 2:

C5 =
$$\frac{b}{a(100k)(\pi)(f_C)}$$
C6 =
$$\frac{a}{4(100k)(\pi)(f_C)}$$

where fc is the desired 3dB corner frequency.

For example, to choose a Butterworth filter response with a corner frequency of 5kHz:

C5 =
$$\frac{1.000}{(1.414)(100k\Omega)(3.14)(5kHz)} \approx 450pF$$

C6 = $\frac{1.414}{(4)(100k\Omega)(3.14)(5kHz)} \approx 225pF$

Choosing standard capacitor values changes C5 to 470pF and C6 to 220pF, as shown in the *Typical Application Circuit*.

Data Slicer

The data slicer takes the analog output of the data filter and converts it to a digital signal. This is achieved by using a comparator and comparing the analog input to a threshold voltage. One input is supplied by the data

Table 2. Coefficents to Calculate C5 and C6

FILTER TYPE	а	b
Butterworth (Q = 0.707)	1.414	1.000
Bessel (Q = 0.577)	1.3617	0.618

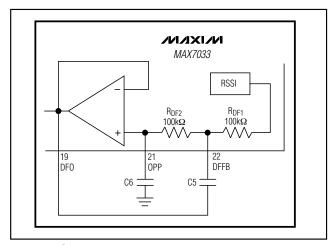


Figure 2. Sallen-Key Lowpass Data Filter

filter output. Both comparator inputs are accessible offchip to allow for different methods of generating the slicing threshold, which is applied to the second comparator input.

The suggested data slicer configuration uses a resistor (R1) connected between DSN and DSP with a capacitor (C4) from DSN to DGND (Figure 3). This configuration averages the analog output of the filter and sets the threshold to approximately 50% of that amplitude. With this configuration, the threshold automatically adjusts as the analog signal varies, minimizing the possibility for errors in the digital data. The values of R1 and C4 affect how fast the threshold tracks to the analog amplitude. Be sure to keep the corner frequency of the RC circuit much lower than the lowest expected data rate.

Note that a long string of zeros or ones can cause the threshold to drift. This configuration works best if a coding scheme, such as Manchester coding, which has an equal number of zeros and ones, is used.

To prevent continuous toggling of DATAOUT in the absence of an RF signal due to noise, add hysteresis to the data slicer as shown in Figure 4.

Peak Detector

The peak-detector output (PDOUT), in conjunction with an external RC filter, creates a DC output voltage equal to the peak value of the data signal. The resistor provides a path for the capacitor to discharge, allowing the peak detector to dynamically follow peak changes of the data-filter output voltage. For faster data slicer response, use the circuit shown in Figure 5.

Layout Considerations

A properly designed PC board is an essential part of any RF/microwave circuit. On high-frequency inputs and outputs, use controlled-impedance lines and keep them as short as possible to minimize losses and radiation. At high frequencies, trace lengths that are on the order of $\lambda/10$ or longer act as antennas.

Keeping the traces short also reduces parasitic inductance. Generally, 1in of a PC board trace adds about 20nH of parasitic inductance. The parasitic inductance can have a dramatic effect on the effective inductance of a passive component. For example, a 0.5in trace connecting a 100nH inductor adds an extra 10nH of inductance or 10%.

To reduce the parasitic inductance, use wider traces and a solid ground or power plane below the signal traces. Also, use low-inductance connections to ground on all GND pins, and place decoupling capacitors close to all VDD connections.

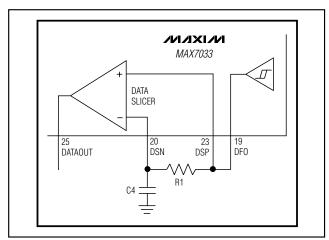


Figure 3. Generating Data Slicer Threshold

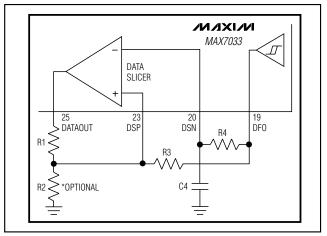


Figure 4. Generating Data Slicer Hysteresis

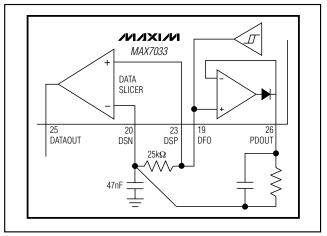
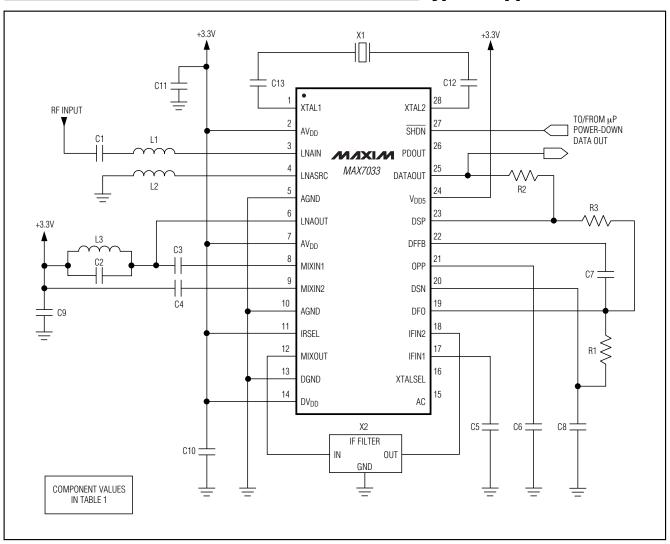


Figure 5. Using PDOUT for Faster Startup

Typical Application Circuit



Chip Information

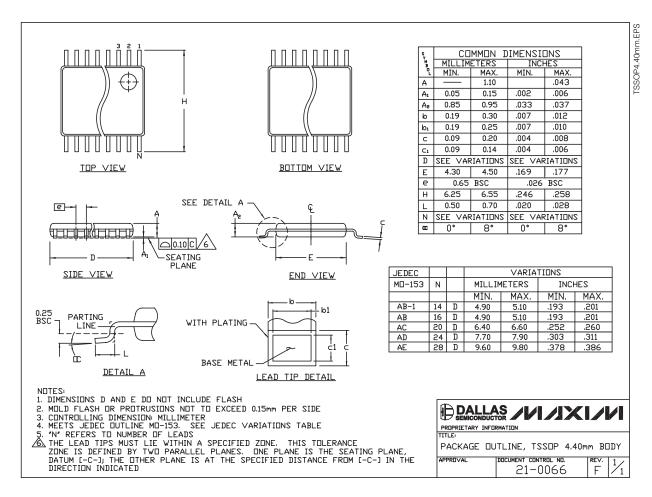
TRANSISTOR COUNT: 3208

PROCESS: CMOS

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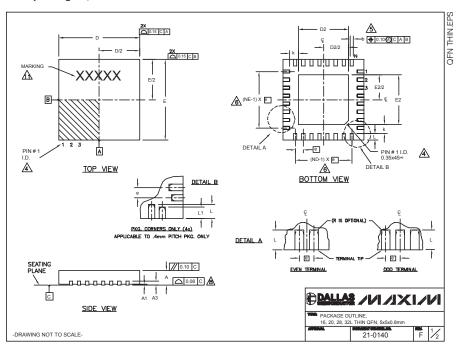
Package Information

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to www.maxim-ic.com/packages.)



Package Information (continued)

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to www.maxim-ic.com/packages.)



COMMON DIMENSIONS											EXPOSED PAD VARIATIONS												
PKG.	KG. 16L 5x5				OL 5>	(5	28L 5x5			32L 5x5				PKG.	D2			E2			L	DOWN	
YMBOL	MIN. NOM. MAX.		MIN. NOM.		MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		CODES	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	±0.15	BONDS ALLOWED		
Α	0.70	0.75	0.80	0.70	0.75	0.80	0.70	0.75	0.80	0.70	0.75	0.80		T1655-1	3.00	3.10	3.20	3.00	3.10	3.20	**	NO	
A1	0	0.02	0.05	0	0.02	0.05	0	0.02	0.05	0	0.02	0.05		T1655-2	3.00	3.10	3.20	3.00	3.10	3.20	**	YES	
A3	0.20 REF.		0.20 REF.			0.20 REF.			0.20 REF.				T1655N-1	3.00	3.10	3.20	3.00	3.10	3.20	**	NO		
b					_	 		_			.25 0.30		T2055-2	3.00	3.10	3.20	3.00	3.10	3.20	**	NO		
D	4.90		5.10	_	_	-	_	5.00	5.10	4.90	5.00	5.10		T2055-3	3.00	3.10	3.20	3.00	3.10	3.20	**	YES	
F	_		5.10	_		-	_		5.10	_		-		T2055-4	3.00	3.10	3.20	3.00	3.10	3.20	**	NO	
e	0.80 BSC		0.65 BSC			0.50 BSC			0.50 BSC				T2055-5	3.15	3.25	3.35	3.15	3.25	3.35	0.40	Y		
k	0.25	00 00	Ĭ.	0.25	00 00	<u> </u>	0.25	.50 D	<u> </u>	0.25	T	<u> </u>		T2855-1	3.15	3.25	3.35	3.15	3.25	3.35	**	NO	
ı	0.25	0.40	0.50		0.55	0.65		0.55	0.65	0.23	0.40	0.50		T2855-2	2.60	2.70	2.80	2.60	2.70	2.80	**	NO	
				0.45	-		0.45		0.05	0.30		-		T2855-3	3.15	3.25	3.35	3.15	3.25	3.35	**	YES	
L1	-	-	-		-	-	-	-	-	-	ļ.,	-		T2855-4	2.60	2.70	2.80	2.60	2.70	2.80	**	YES	
N	16		20			28			32				T2855-5	2.60	2.70	2.80	2.60	2.70	2.80	**	NO		
ND	4		5 5			7			8 8				T2855-6	3.15	3.25	3.35	3.15	3.25	3.35	**	NO		
NE			-						-				T2855-7	2.60	2.70	2.80	2.60	2.70	2.80	**	YES		
JEDEC	WHHB		WHHC			WHHD-1			WHHD-2				T2855-8	3.15	3.25	3.35	3.15	3.25	3.35	0.40	Y		
TC.														T2855N-1	3.15	3.25	3.35	3.15	3.25	3.35	**	N NO	
TES: 1. DIMENSIONING & TOLERANCING CONFORM TO ASME Y14.5M-1994.											T3255-2	3.00	3.10	3.20	3.00	3.10	3.20	**					
ALL DIMENSIONS ARE IN MILLIMETERS. ANGLES ARE IN DEGREES.										T3255-3 T3255-4	3.00	3.10	3.20	3.00	3.10	3.20		YES NO					
N IS THE TOTAL NUMBER OF TERMINALS.									T3255N-1	3.00	3.10	3.20			0.20		NO NO						
THE TE CONFO	RMIN/ ORM TO NAL, B	AL #1 I D JESE UT MU	DENTIF 0 95-1 S IST BE	IER AI SPP-01 LOCAT	ND TER 2. DET	RMINAL TAILS O	OF TER	MINAL NE INI	#1 IDE	NTIFI	ER ARE	Ξ		13255N-1	3.00	3.10	3.20	3.00	3.10 SEE CO	3.20 MMON E		INS TABLE	
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COPLA	NARIT	Y APPI	LIES TO) THE	EXPOS	SED HE	AT SIN	IK SLL	JG AS 1	NELL A	AS THE	TERN	IALS.										
	VING CONFORMS TO JEDEC MO220, EXCEPT EXPOSED PAD DIMENSION FOR T2855-1, 3-3 AND T2855-6:														LA	B /		413	<1/1				
WARPA	GE SH	IALL N	OT EX	CEED (0.10 mr	n.												NO TO	M				
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